The RF Line NPN Silicon High-Frequency Transistors

Designed primarily for use in high–gain, low–noise, small–signal UHF and microwave amplifiers constructed with thick and thin–film circuits using surface mount components.

• T1 suffix indicates tape and reel packaging of 3,000 units per reel.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	15	Vdc
Collector-Base Voltage	VCBO	20	Vdc
Emitter-Base Voltage	V _{EBO}	2.0	Vdc
Collector Current — Continuous	IC	25	mAdc
Maximum Junction Temperature	T _{Jmax}	150	°C
Power Dissipation, T _{Case} = 75°C Derate linearly above T _{Case} = 75°C @	PD(max)	0.273 3.64	W mW/°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Storage Temperature	T _{stg}	-55 to +150	°C
Thermal Resistance Junction to Case	$R_{ extsf{ heta}JC}$	275	°C/W

DEVICE MARKING

BFR92ALT1 = P2

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (1) $(I_C = 10 \text{ mA})$	V _(BR) CEO	15	-	Vdc
Collector–Base Breakdown Voltage $(I_C = 100 \ \mu A)$	V _(BR) CBO	20	-	Vdc
Emitter–Base Breakdown Voltage (I _C = 100 μ A)	V(BR)EBO	2.0	-	Vdc
Collector Cutoff Current (V _{CB} = 10 V)	ICBO		50	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = 14 \text{ mA}, V_{CE} = 10 \text{ V}$)	hFE	40	_	_
Collector–Emitter Saturation Voltage (1) ($I_C = 25 \text{ mA}, I_B = 5.0 \text{ mA}$)	V _{CE(sat)}	—	0.5	Vdc
Base–Emitter Saturation Voltage (1) (I _C = 25 mA, I _B = 5.0 mA)	V _{BE(sat)}	—	1.2	Vdc

NOTE:

REV 7

1. Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.



(continued)



RF TRANSISTORS NPN SILICON

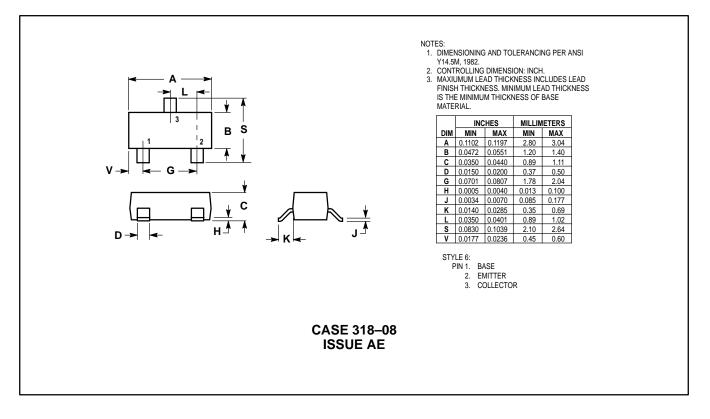


CASE 318-08, STYLE 6 SOT-23 LOW PROFILE

ELECTRICAL CHARACTERISTICS — continued (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Тур	Unit
SMALL-SIGNAL CHARACTERISTICS			
Current–Gain — Bandwidth Product ($I_C = 14 \text{ mA}, V_{CE} = 10 \text{ V}, f = 500 \text{ MHz}$)	fT	4.5	GHz
Noise Figure (V _{CE} = 1.5 V, I _C = 3.0 mA, R _S = 50 Ω , f = 500 MHz)	NF	3.0	dB
Capacitance–Collector to Base (V _{CB} = 10 Vdc, f = 1.0 MHz)	C _{cb}	0.7	pF

PACKAGE DIMENSIONS



Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death Motorola was negligent regarding the design or manufacture of the part. Motorola and the are registered trademarks of Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447 JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki, 6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

0



HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298

